

Shubhadeep Bhattacharjee

List of Publications by Year in descending order

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Version: 2024-02-01

21
papers

438
citations

840776

11
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839539

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21
all docs

21
docs citations

21
times ranked

565
citing authors

#	ARTICLE	IF	CITATIONS
1	Out-of-equilibrium criticalities in graphene superlattices. <i>Science</i> , 2022, 375, 430-433.	12.6	34
2	Interfacial ferroelectricity in marginally twisted 2D semiconductors. <i>Nature Nanotechnology</i> , 2022, 17, 390-395.	31.5	115
3	Gallium Selenide Nanoribbons on Silicon Substrates for Photodetection. <i>ACS Applied Nano Materials</i> , 2021, 4, 7820-7831.	5.0	5
4	Large-area growth of MoS ₂ at temperatures compatible with integrating back-end-of-line functionality. <i>2D Materials</i> , 2021, 8, 025008.	4.4	14
5	Insights into Multilevel Resistive Switching in Monolayer MoS ₂ . <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 6022-6029.	8.0	54
6	Emulating synaptic response in n- and p-channel MoS ₂ transistors by utilizing charge trapping dynamics. <i>Scientific Reports</i> , 2020, 10, 12178.	3.3	21
7	Effects of Annealing Temperature and Ambient on Metal/PtSe ₂ Contact Alloy Formation. <i>ACS Omega</i> , 2019, 4, 17487-17493.	3.5	10
8	Adaptive Transport in High Performance (I on), Steep Sub-Threshold Slope (SS < 60 mV/dec) MoS ₂ Transistors. <i>IEEE Nanotechnology Magazine</i> , 2019, 18, 1071-1078.	2.0	2
9	Hole Injection and Rectifying Heterojunction Photodiodes through Vacancy Engineering in MoS ₂ . <i>Advanced Electronic Materials</i> , 2019, 5, 1800863.	5.1	7
10	Two-Dimensional Materials and Their Role in Emerging Electronic and Photonic Devices. <i>Electrochemical Society Interface</i> , 2018, 27, 53-58.	0.4	5
11	Optoelectronics based on Vertical Transport in Multi-layer MoS ₂ . , 2018, , .		1
12	Nitride Dielectric Environments to Suppress Surface Optical Phonon Dominated Scattering in High-Performance Multilayer MoS ₂ FETs. <i>Advanced Electronic Materials</i> , 2017, 3, 1600358.	5.1	20
13	(Invited) Interface Engineering of High-k Dielectrics and Metal Contacts for High Performance Top-Gated MoS ₂ FETs. <i>ECS Transactions</i> , 2017, 80, 101-107.	0.5	3
14	A sub-thermionic MoS ₂ FET with tunable transport. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	32
15	Realizing P-FETs and photodiodes on MoS ₂ through area-selective p-doping via vacancy engineering. , 2017, , .		0
16	High Performance HfO ₂ Back Gated Multilayer MoS ₂ transistors. <i>IEEE Electron Device Letters</i> , 2016, , 1-1.	3.9	31
17	Surface State Engineering of Metal/MoS ₂ Contacts Using Sulfur Treatment for Reduced Contact Resistance and Variability. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2556-2562.	3.0	44
18	Intrinsic Limit for Contact Resistance in Exfoliated Multilayered MoS ₂ FET. <i>IEEE Electron Device Letters</i> , 2016, 37, 119-122.	3.9	18

#	ARTICLE	IF	CITATIONS
19	Optical-Phonon-Limited High-Field Transport in Layered Materials. IEEE Transactions on Electron Devices, 2016, 63, 767-772.	3.0	7
20	Early Detection of Breast Cancer: Synthesis and Characterization of Novel Target Specific NIR-Fluorescent Estrogen Conjugate for Molecular Optical Imaging. Journal of Fluorescence, 2011, 21, 1171-1177.	2.5	15
21	Early detection of breast cancer: a molecular optical imaging approach using novel estrogen conjugate fluorescent dye. , 2011, , .		0